

8-11 0920 #2

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Satoshi INOUE et al.

Application No.: 09/899,058

Filed: July 6, 2001

Docket No.: 110041

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURE

INFORMATION DISCLOSURE STATEMENT

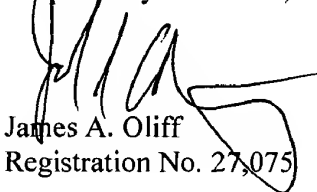
Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of the reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the reference is discussed in the present specification.

Respectfully submitted,


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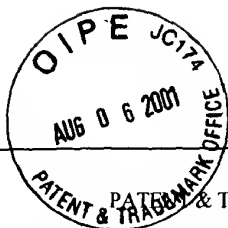
JAO:JSA/zmc

Date: August 6, 2001

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Sheet 1 of 1Form PTO-1449
(REV. 8-83)

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

US Dept. of Commerce
PATENT & TRADEMARK OFFICEATTY DOCKET NO.
110041APPLICATION NO.
09/899,058APPLICANT(S)
Satoshi INOUE et al.FILING DATE
July 6, 2001

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

		✓ Ya-Chin KING et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si _{1-x} Ge _x ", IEDM, 1998 pp 115-118

EXAMINER

DATE CONSIDERED

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.